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AMENDMENT TO THE SPECIFICATION

Please amend the specification by deleting the text that was added to the specification after Table 12 on page 31 and which reads as follows (and is struck-through):

parameters using the following equipment at the following operating conditions: The samples were in powder form and were prepared for analysis by adding a small amount of NIST (National Institute of Standards and Testing) silicon metal powder. The NIST silicon metal powder is a certified standard material that is used to correct the peak position calculations for errors in instrument alignment. This powder blend, i.e., the powder blend of the sample powder and the NIST silicon metal powder, was mixed with an organic binder and acctone to form a slurry. The resulting slurry was affixed to a glass slide and then allowed to dry:

peak resolution. Data was collected using as a minimum a 0.008 degrees step in the range of 75 degrees to 135 degrees. These step positions were selected so as to maximum the accuracy of the peak position determination. Data was collected for four seconds at each step. Collected diffraction data was first corrected for instrument error using the NIST silicon reference pattern. Precise diffraction peak positions were determined by fitting a pseudo-Voight function to the collected data. Lattice parameters for each of the SiAlON phases were determined from the peak positions by using a "least squares" method. The resultant parameter errors are set forth in parenthesis for the alpha prime SiAlON phase and the beta prime SiAlON phase of each example.

Table 13 below sets forth the results of these lattice parameter measurements where these lattice parameters measurements have an error of ± .0001, except where indicated by an asterisk (*) that shows no error in the measurement.

Table 13

Results of Lattice Parameter Measurement for Samples 982, 1145A, 1145B and 1374D

Semple Beta Alpha Alpha Beta Silloon Lettice Lettice Lettice Lettice Parameter Parameter Parameter 'a' 'c' 'a'	Beta X-Value m-Value a-Value (3-x) Parameter
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				_,				
	(wt.%)							
1145A	6%	7.7977	5.8759	7.6204	2:0188*	0.354	1.063	0.478
		7.7928	5.6711	7.6203	2.9201*	0.321	0.063	0.487
4145B	2%					0.319	0.957	0.475
982	1.5%	7.7927	5.6706	7.6201	2,9197			
1374D	0%	7.7875	5.6665	7.6223	2.9215	0.287	0.860	0.542

Table 14 below sets forth the content of the alpha SiAION phase in weight percent of the two phase composite (i.e., the alpha SiAION phase and the beta SiAION phase), the formula of the alpha SiAION phase, and the ytterbium content (in moles) contained in the grain boundary for the four camples of Table 13.

Table 14

The Content of Alpha SiAION Phase in the Two Phase Composite, the Formula of the Alpha SiAION Phase and the Ytterbium Content (in moles) Contained in the Grain Boundary for Samples 982, 1145A, 1145B and 1374D

Sample/ %- Beta in the Starting Silicon Nitride Powder	Weight % alpha SIAION	Formula for Alpha SiAION	Moles of Yb in the Grain Boundary
1146A [6%]	37.7 %	Ybo.35 Sho.01 Als.90 Oo.93 Al	0.0282
1145B [2%]	42.7%	Ybo.32 Siso.16 Als.85 Oo.88 Ns6.41	0.0277
<u>-982 [1.5%]</u>	47.1 %	¥b0,32.Si10.38 Al1.52 Op.87 N15.13	0.0263
1374D-[0%]	62.7%	Ybo.29 Si 10.48 Als. 52 Oo.66 N15.34	0.0217

The formula for alpha SiAION phase is Yb_xSi_{13 (m+n)}Al_(m+n)O_nN_{16 n}. The values of "x" and "z" are calculated from the lattice parameters measurements using the following formula: a=7.75±0.139x and e=5.62±0.153x, units are in angstroms. Equations are from Z.Shen, T. Ekstrom, and M. Nygren, Ytterbium-Stabilized a sialon ceramics, J. Phys. D: Appl. Phys. 29 (1998). The value of "m" is equal to three times the value of "x". The value of "n" is estimated from calculations based upon the overall composition of the alpha SiAION phase, the phase density of the alpha SiAION phase, the "z" value, and the beta SiAION content from the x-ray diffraction results. These calculations are as described as follows: a=7.60442±0.03z and c=2.90751±0.027z.

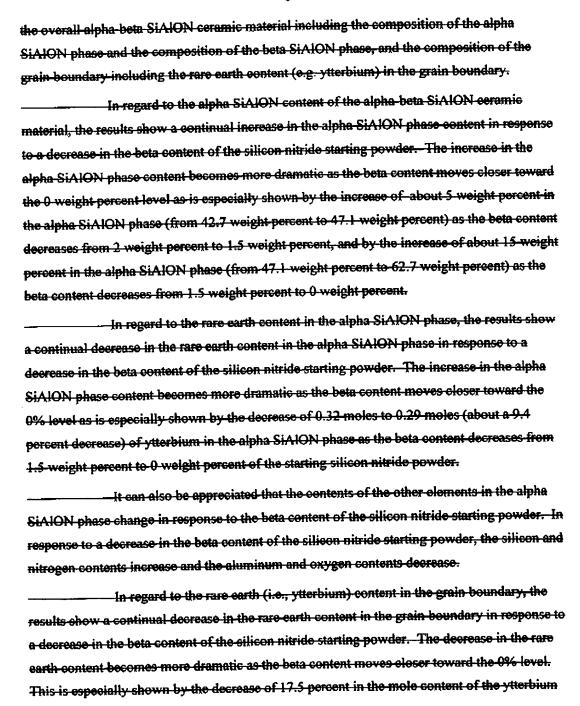
Referring to the results set forth in Table 13 and Table 14, in its broader appears it is apparent that there exists a relationship between the content of beta silicon nitride in the silicon nitride starting powder and each one of the following: the amount of alpha SiAION phase that is present in the alpha beta SiAION ceramic material, the composition of

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in the grain boundary as the beta content decreases from 1.5 weight percent to 0 weight	
percent.	
It is also the case that the content of beta silicon nitride in the silicon nitride	
starting powder impacts the beta-SiAlON phase wherein the starting silicon nitride powder	
that had no beta silicon nitride formed a beta-SiAlON phase with a higher "z" value. In thi	S
regard, the "z" value of the beta SiAION phase that was formed from a silicon nitride starti	
powder that did not have any beta phase was 0.542, which was 11.3 percent greater than the	ю
"z" value of a beta SiAlON phase formed from a starting silicon nitride powder that had a	
weight percent beta content.	
It can thus be seen that the content of beta silicon nitride has an impact on	
aspects that influence properties of the alpha-beta SiAlON ceramic, and hence, impact the	
performance of the alpha-beta SiAION ceramic product as, for example, a cutting tool. M	ore
specifically, these changes affect the thermal conductivity, thermal expansion and Young's	5
Modulus of the ceramic, and these properties influence tool performance.	